advanced

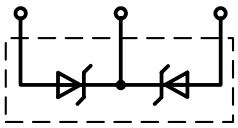
Schottky

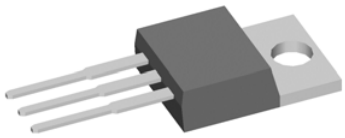
V_{RRM} = 100 V
I_{FAV} = 2x 40 A
V_F = 0.73 V

High Performance Schottky Diode
Low Loss and Soft Recovery
Common Cathode

Part number *(Marking on product)*

DSA 80 C 100PB





Features / Advantages:

- Very low Vf
- Extremely low switching losses
- Low Irm-values
- Improved thermal behaviour
- High reliability circuit operation
- Low voltage peaks for reduced protection circuits
- Low noise switching
- Low losses

Applications:

- Rectifiers in switch mode power supplies (SMPS)
- Free wheeling diode in low voltage converters

Package:

TO-220AB

- Industry standard outline
- Epoxy meets UL 94V-0
- RoHS compliant

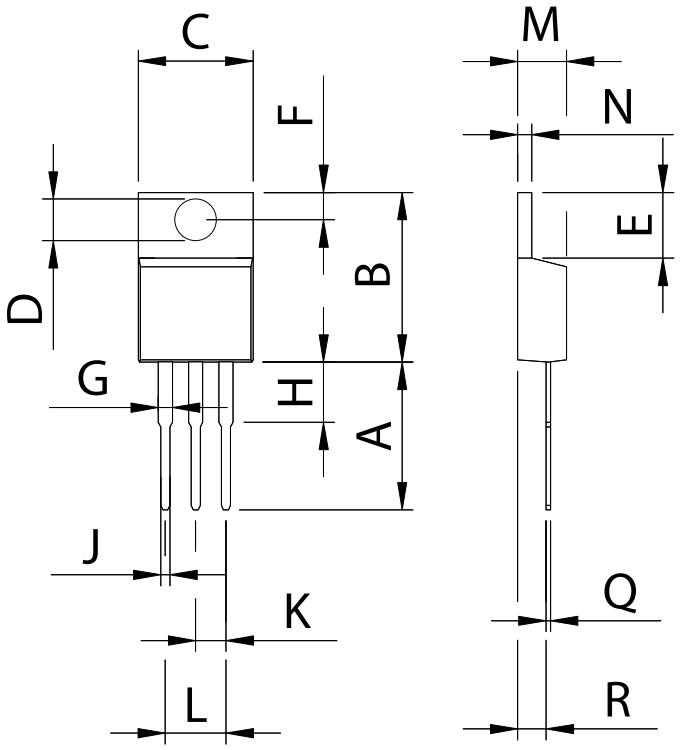
Symbol	Definition	Conditions		Ratings min.	typ.	max.	Unit
V_{RRM}	*max. repetitive reverse voltage*		T_{VJ} = 25 °C			100	V
I_R	*reverse current*	V_R = 100 V	T_{VJ} = 25 °C			0.7	mA
		V_R = 100 V	T_{VJ} = 125 °C			7	mA
V_F	*forward voltage*	I_F = 40 A	T_{VJ} = 25 °C			0.91	V
		I_F = 80 A				1.10	V
		I_F = 40 A	T_{VJ} = 125 °C			0.73	V
		I_F = 80 A				0.95	V
I_{FAV}	*average forward current*	rectangular, d = 0.5	T_C = 150 °C			40	A
V_{F0}	*threshold voltage* } *for power loss calculation only*		T_{VJ} = 175 °C			0.44	V
r_F	*slope resistance* }					6.5	mΩ
R_{thJC}	*thermal resistance junction to case*					0.60	K/W
T_{VJ}	*virtual junction temperature*			-55		175	°C
P_{tot}	*total power dissipation*		T_C = 25 °C			250	W
I_{FSM}	*max. forward surge current*	t_p = 10 ms (50 Hz), sine	T_{VJ} = 45 °C			400	A
C_J	*junction capacitance*	V_R = V; f = 1 MHz	T_{VJ} = 25 °C				pF
E_{AS}	*non-repetitive avalanche energy*	I_{AS} = 10 A; L = 100 µH	T_{VJ} = 25 °C			5	mJ
I_{AR}	*repetitive avalanche current*	V_A = 1.5·V_R typ.; f = 10 kHz				1	A

advanced

Symbol	Definition	Conditions	Ratings min.	typ.	max.	Unit
I_{RMS}	*RMS current*	per pin*			35	A
R_{thCH}	*thermal resistance case to heatsink*			0.50		K/W
M_D	*mounting torque*		0.4		0.6	Nm
F_C	*mounting force with clip*		20		60	N
T_{stg}	*storage temperature*		-55		150	°C
Weight				2		g

* Irms is typically limited by: 1. pin-to-chip resistance; or by 2. current capability of the chip.
In case of 1, a common cathode/anode configuration and a non-isolated backside, the whole current capability can be used by connecting the backside.

Outlines TO-220AB



Dim.	Millimeter Min.	Max.	Inches Min.	Max.
A	12.70	13.97	0.500	0.550
B	14.73	16.00	0.580	0.630
C	9.91	10.66	0.390	0.420
D	3.54	4.08	0.139	0.161
E	5.85	6.85	0.230	0.270
F	2.54	3.18	0.100	0.125
G	1.15	1.65	0.045	0.065
H	2.79	5.84	0.110	0.230
J	0.64	1.01	0.025	0.040
K	2.54	BSC	0.100	BSC
M	4.32	4.82	0.170	0.190
N	1.14	1.39	0.045	0.055
Q	0.35	0.56	0.014	0.022
R	2.29	2.79	0.090	0.110